

东莞市华远电子有限公司

DONG GUAN SHI HUA YUAN ELECTRON CO..LTD.

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TO-92 Plastic-Encapsulate Transistors

2SA673

TRANSISTOR (PNP)

FEATURE

Power dissipation

P_{CM} : 0.4 W (Tamb=25)

Collector current

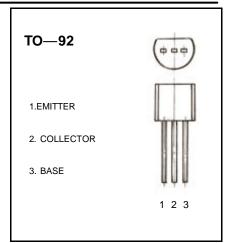
I_{CM:} -0.5 A

Collector-base voltage

 $V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150



ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	Ic= -10 μ A , I _E =0	-35			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I_C =-1 mA , I_B =0	-35			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E =-10 μ A , I _C =0	-4			V
Collector cut-off current	Ісво	V _{CB} = -20 V , I _E =0			-0.5	μА
DC current gain	h _{FE (1)} *	V _{CE} =-3V, I _C = -10mA	60		320	
	h _{FE(2)}	V _{CE} =-3 V, I _C =-500mA	10			
Collector-emitter saturation voltage	V _{CEsat} *	I _C = -150mA, I _B =-15mA			-0.6	V
Base-emitter voltage	V _{BE}	V _{CE} =-3 V, I _C =-10mA			-0.75	V

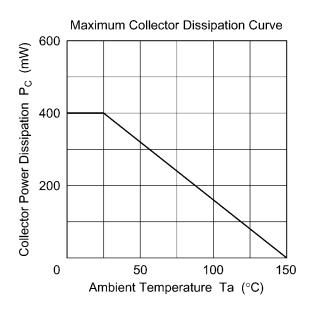
^{*}Measured using pulse

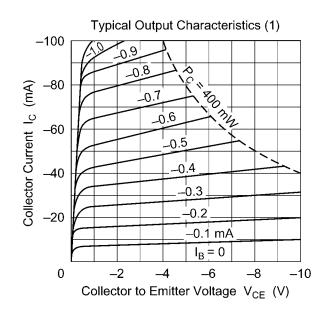
CLASSIFICATION OF h_{FE(1)}

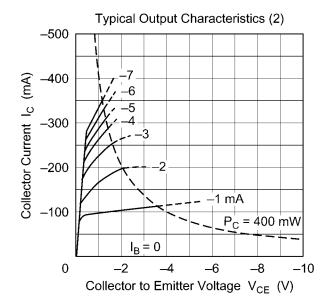
Rank	В	С	D
Range	60-120	100-200	160-320

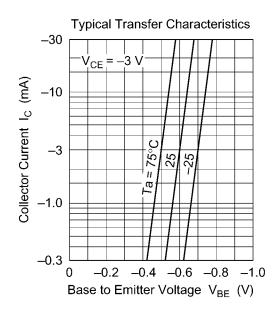
Typical characteristics

2SA673









TO-92 PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.400	4.700	0.173	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.270TYP		0.050TYP		
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ö		1.600		0.063	
$\overline{}$	0.000	0.380	0.000	0.015	